



Future Challenges Facing SEE Pulsed Laser Technique

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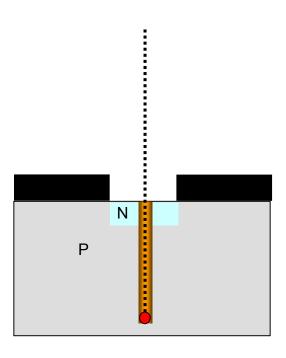
What is the Basic Mechanism Behind Single Event Effects?

CHARGE INJECTION



Charge Injection by Ion Beam



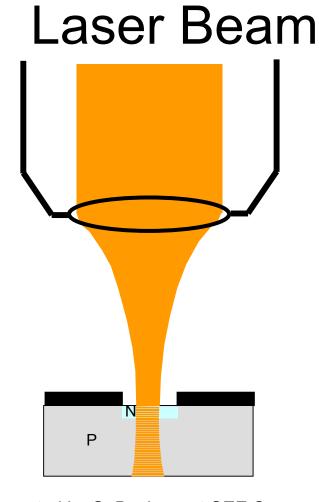




Charge Injection

by Pulsed Focused





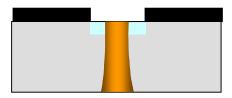


Charge Injection

by Pulsed Focused





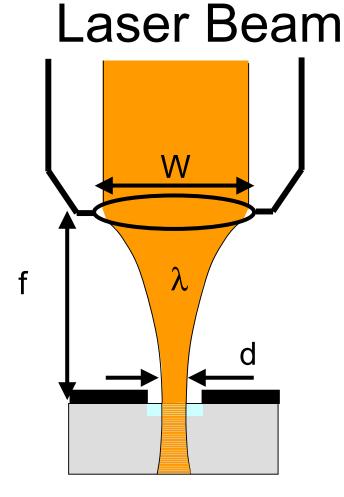




Charge Injection

by Pulsed Focused





 $d = 2.44\lambda f$







- Light must be able to reach sensitive nodes
 - Metal layers and packaging
- Light must be able to create free carriers
 - Materials and structures

Preferences

- Sensitive node must be "visible"
 - Scaling
- Amount of absorbed light must be measurable
 - Quantifiable





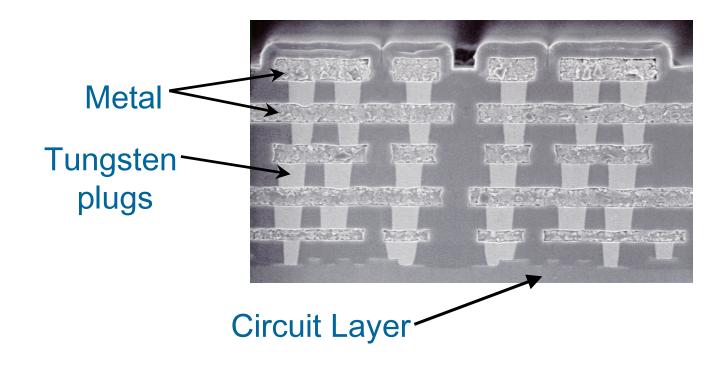
Future Challenges







Metallization

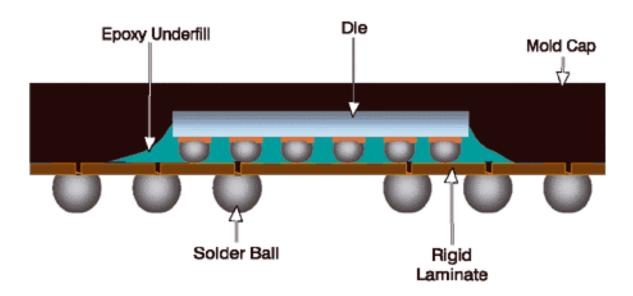








- Metallization
- Packaging

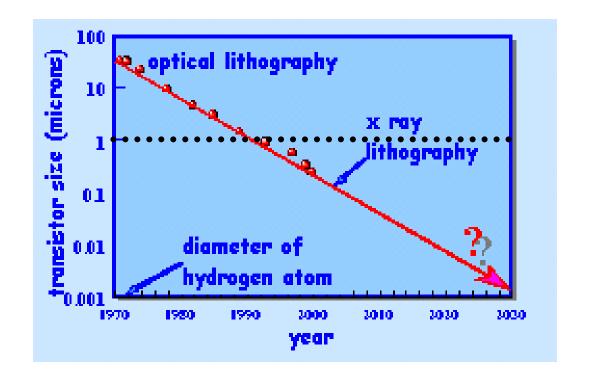






Future Challenges

- Metallization
- Packaging
- Scaling

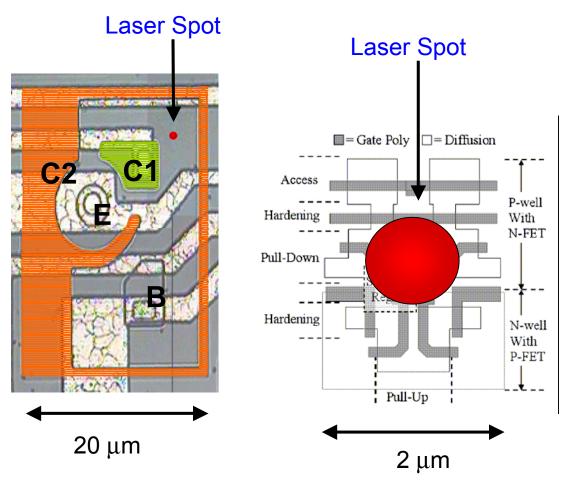








- Metallization
- Packaging
- Scaling

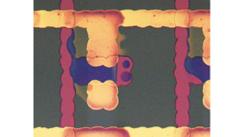




Future Challenges



- Metallization
- Packaging
- Scaling

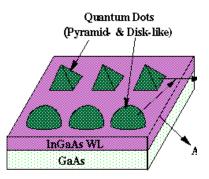


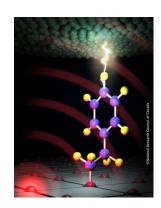
Plastic Transistor



Exotic Materials

Quantum Dots





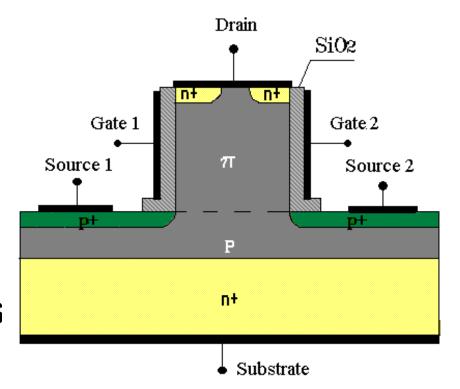
Single Molecule Transistor







- Metallization
- Packaging
- Scaling
- Exotic Material
- Novel Structures

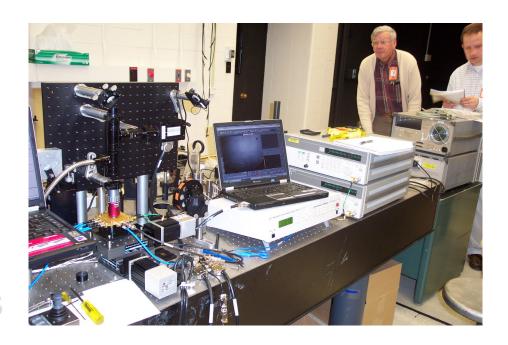




Future Challenges



- Metallization
- Packaging
- Scaling
- Exotic Material
- Novel Structures
- Equipment



\$\$ for LasersLarge Optical Table



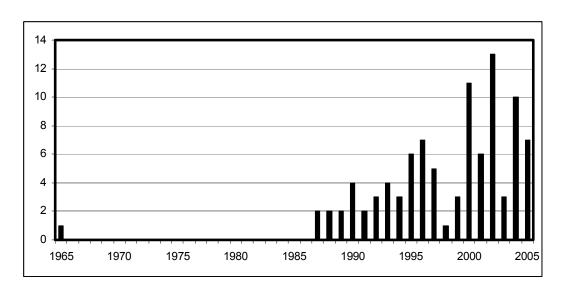


Current State of Technique











Major US Sponsor: DTRA



5 Facilities



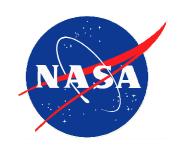
European Aeronautic MBDA (England) **Defense & Space Company (France)** NRL (USA) Aerospace (USA)

> Presented by S. Buchner at SEE Symposium, Long Beach, CA April 11th, 2006

IXL (France)



Pulsed Laser Can Produce ...



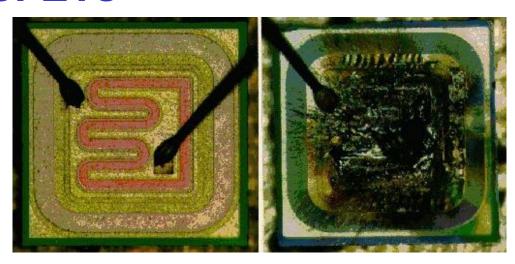
- Single Event Transient (SET)
- Single Event Upset (SEU)
- Single Event Latchup (SEL)
- Single Event Snapback (SES)
- Dose Rate (γ-dot)



Pulsed Laser Not Practical for....



- Single Event Gate Rupture
- Single Event Burnout in Power MOSFETs

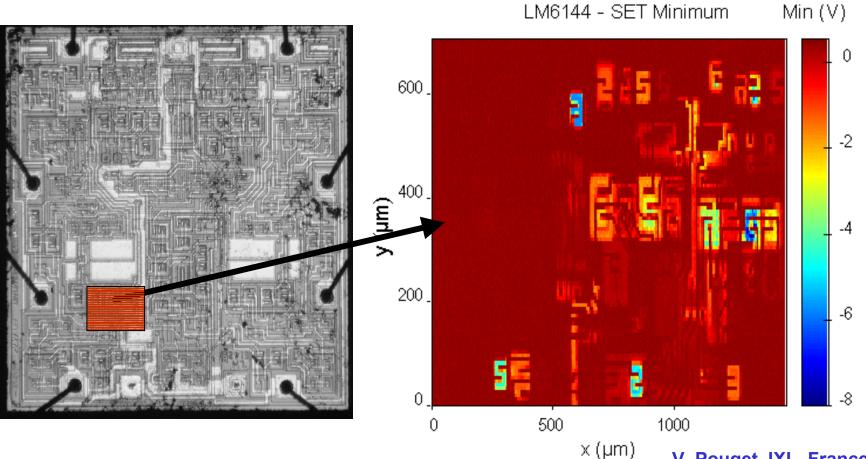


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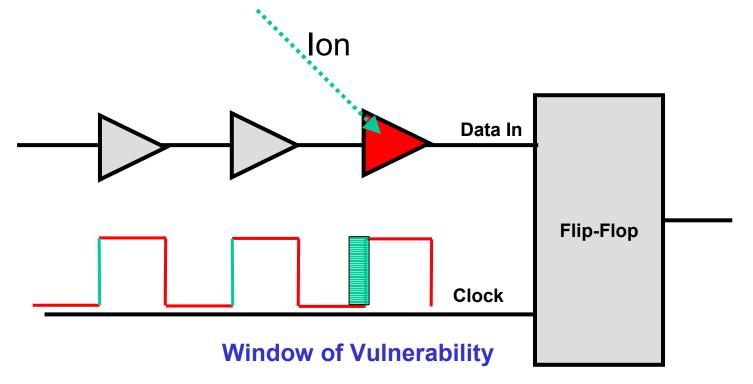


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Temporal Information

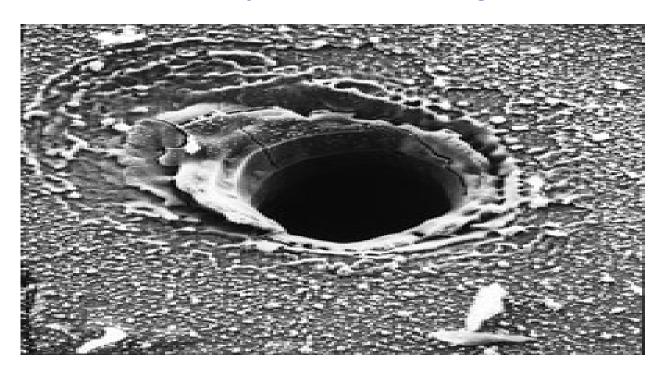




Very High LET



LET >> 100 MeV.cm²/mg Limited by material damage





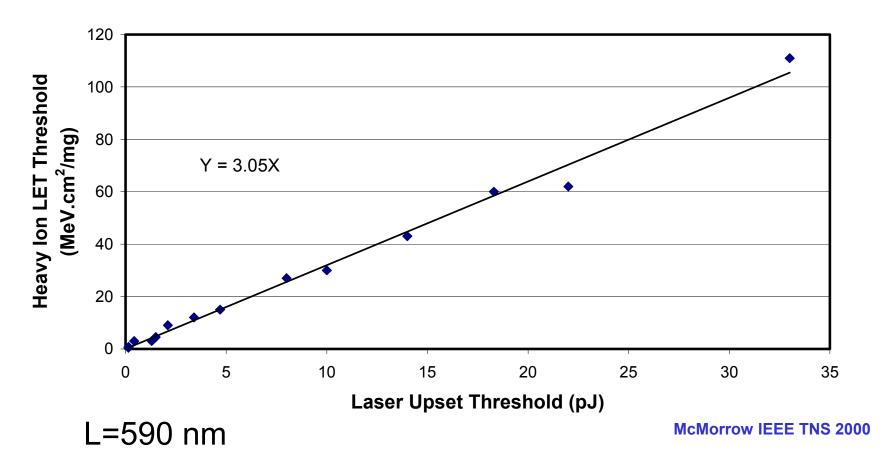






Ion LET Threshold from Laser Energy Threshold?

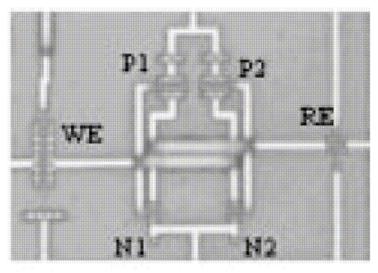


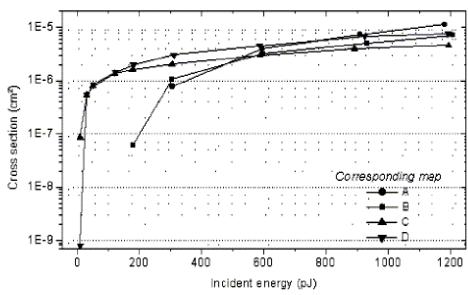












- · No metal.
- Large structures.

V. Pouget, IXL, France



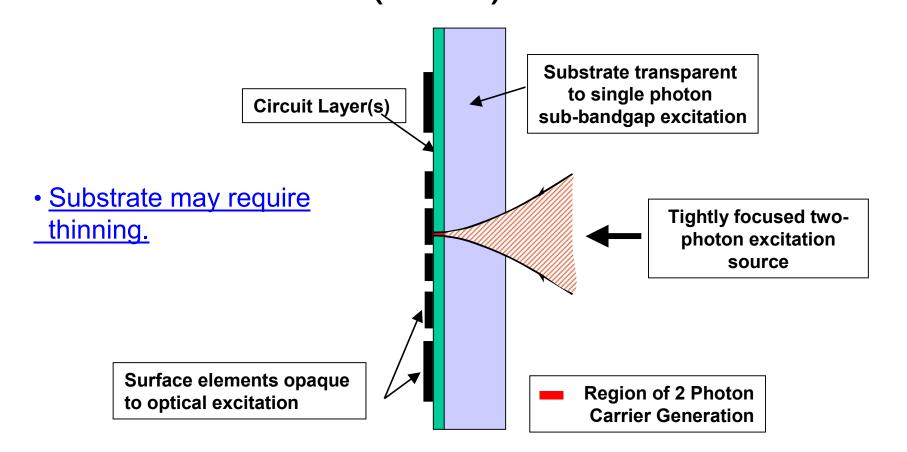


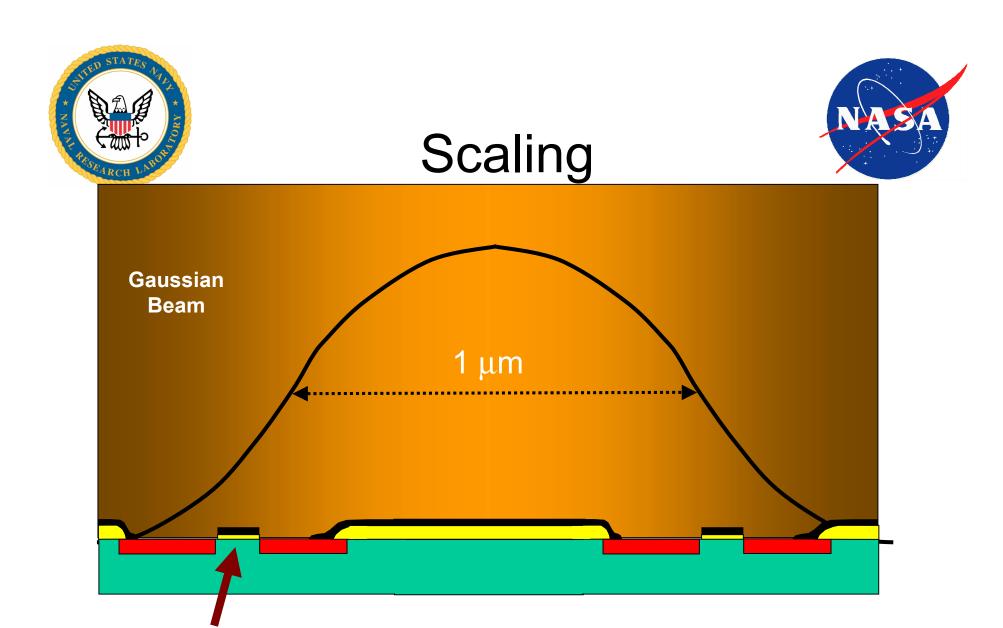




Two Photon Absorption (TPA)







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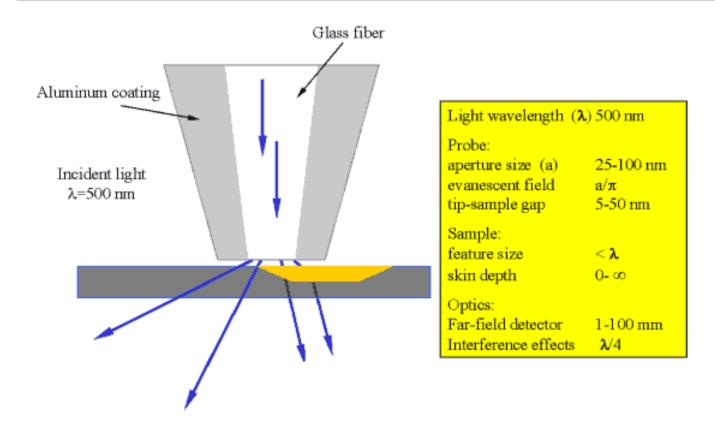
Gate Length = 0.1 μm











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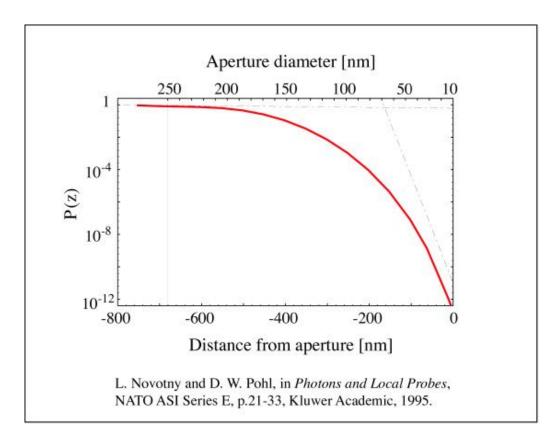




Scaling

Aperture Limits
Pulse Energy

XRAYS

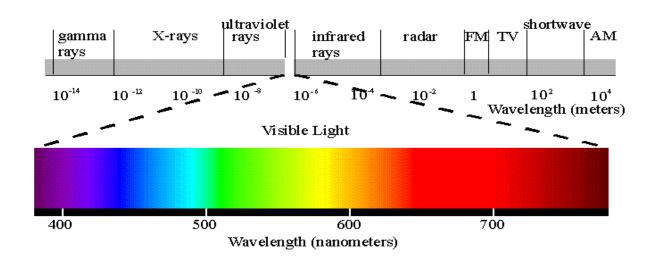






Exotic Materials

Adjust the wavelength to ensure absorption.





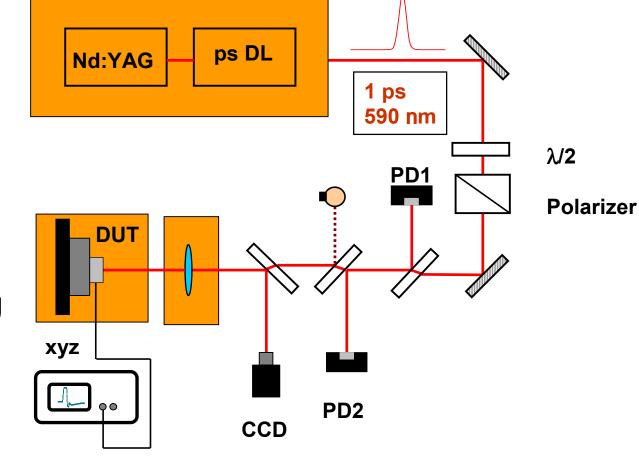




1. Laser

2. Stage

3. Focusing Optics









- < 100 ps pulse width
- Single shot to 100 MHz
- Pulse Energy = 8 pJ
- Multiple wavelengths



Not sufficient intensity for TPA







- Challenges for the pulsed laser:
 - Metal
 - Package
 - Scaling
 - Exotic materials
 - Novel devices
 - Equipment